

Customer No.: 31561  
Application No.: 10/710,818  
Docket NO.: 14217-US-PA-X

**AMENDMENT**

**In The Claims:**

Claim 1. (previously presented) An electrostatic discharge (ESD) protection device,  
comprising:

an ESD protection circuit, comprising:

at least a diode connected in series between a first voltage and a pad; and

at least an ESD component connected in series between a second voltage and a pad,

wherein each of the at least an ESD component comprises a deep N-well region formed in a P-type substrate, a triple P-well formed in the deep N-well region, and a highly doped N-type (N+) region and a highly doped P-type (P+) region formed in the triple P-well region.

Claim 2. (original) The ESD protection device of claim 1, wherein when a number of the ESD component is one, the N+ region of the ESD component is connected to the pad, and the P+ region of the ESD component is connected to the second voltage.

Claim 3. (original) The ESD protection device of claim 1, wherein when a number of the ESD component is two including a 1<sup>st</sup> ESD component and a 2<sup>nd</sup> ESD component, the N+ region of a 1<sup>st</sup> ESD component is connected to the pad, the P+ region of the 2<sup>nd</sup> ESD component is connected to the second voltage, and the P+ region of the 1<sup>st</sup> ESD component is connected to the N+ region of the 2<sup>nd</sup> ESD component.

Claim 4. (original) The ESD protection device of claim 1, wherein when a number of the ESD component is S including a 1<sup>st</sup> ESD component to a S<sup>th</sup> ESD component, the N+ region of

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the 1<sup>st</sup> ESD component is connected to the pad, the P+ region of the S<sup>th</sup> ESD component is connected to the second voltage, and the P+ region of the T<sup>th</sup> ESD component is connected to the N+ region of the (T+1)<sup>th</sup> ESD component, wherein S is a positive integer and T is a positive integer from 1 to S-1.

Claim 5. (original) The ESD protection device of claim 1, wherein each of the at least a diode comprises a N-well region formed in a P-type substrate, and a N+ region and a P+ region formed in the N-well region.

Claim 6. (original) The ESD protection device of claim 1, wherein when a number of the diode is one, the N+ region of the diode is connected to the first voltage, and the P+ region of the diode is connected to the pad.

Claim 7. (original) The ESD protection device of claim 1, wherein when a number of the diode is two including a first diode and a second diode, the N+ region of a first diode is connected to the first voltage, the P+ region of the second diode is connected to the pad, and the P+ region of the first diode is connected to the N+ region of the second diode.

Claim 8. (original) The ESD protection device of claim 1, wherein when a number of the diode is S including a 1<sup>st</sup> diode to a S<sup>th</sup> diode, the N+ region of the 1<sup>st</sup> diode is connected to the first voltage, the P+ region of the S<sup>th</sup> diode is connected to the pad, and the P+ region of the T<sup>th</sup> diode is connected to the N+ region of the (T+1)<sup>th</sup> diode, wherein S is a positive integer and T is a positive integer from 1 to S-1.

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Claim 9. (original) The ESD protection device of claim 1, wherein the ESD protection device further comprises another ESD protection circuit comprising:

a PMOS transistor; and

an NMOS transistor, wherein a gate of the PMOS transistor and a gate of the NMOS transistor are connected to the pad, a source of the PMOS transistor is connected to a drain of the NMOS transistor, a drain of the PMOS transistor is connected to the first voltage, and a source of the NMOS transistor is connected to the second voltage.

Claim 10. (original) The ESD protection device of claim 1, wherein the ESD protection device is a radio frequency (RF) ESD protection device.

Claims 11-19. (canceled)